

RGTVX6TS65

650V 80A Field Stop Trench IGBT

V_{CES}	650V
I _{C(100°C)}	80A
V _{CE(sat) (Typ.)}	1.5V
P_D	404W

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching & Low Switching Loss
- 3) Short Circuit Withstand Time 2µs
- 4) Pb free Lead Plating; RoHS Compliant

Applications

Solar Inverter

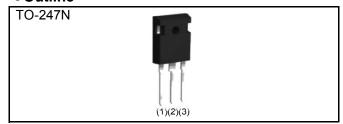
UPS

Welding

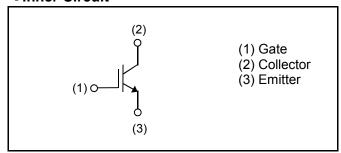
ΙH

PFC

Outline



●Inner Circuit



Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
Typo	Tape Width (mm)	-
Type	Basic Ordering Unit (pcs)	450
	Packing Code	C11
	Marking	RGTVX6TS65

● Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit	
Collector - Emitter Voltage		V _{CES}	650	V	
Gate - Emitter Voltage		V_{GES}	±30	V	
Collector Current	T _C = 25°C	I _C	144	А	
	T _C = 100°C	I _C	80	А	
Pulsed Collector Current		I _{CP} *1	320	А	
Power Dissipation	T _C = 25°C	P _D	404	W	
	T _C = 100°C	P _D	202	W	
Operating Junction Temperature		T _j	-40 to +175	°C	
Storage Temperature		T _{stg}	-55 to +175	°C	

^{*1} Pulse width limited by T_{imax}.

●Thermal Resistance

Parameter	Symbol	Values			Unit
raiametei		Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	0.37	°C/W

ullet IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
r ai ainietei	Syllibol		Min.	Тур.	Max.	Offic
Collector - Emitter Breakdown Voltage	BV _{CES}	$I_{C} = 10 \mu A, V_{GE} = 0 V$	650	-	1	V
Collector Cut - off Current	I _{CES}	V _{CE} = 650V, V _{GE} = 0V	1	1	10	μΑ
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 30V, V_{CE} = 0V$	ı	ı	±200	nA
Gate - Emitter Threshold Voltage	$V_{\text{GE(th)}}$	$V_{CE} = 5V, I_{C} = 57.1 \text{mA}$	5.0	6.0	7.0	V
Collector - Emitter Saturation Voltage	V _{CE(sat)}	I_C = 80A, V_{GE} = 15V T_j = 25°C T_j = 175°C	-	1.5 1.85	1.9 -	V

ullet IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Darameter	Cymphal	Conditions		Unit		
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Input Capacitance	C_{ies}	V _{CE} = 30V	-	4810	-	
Output Capacitance	C _{oes}	V _{GE} = 0V	-	184	-	pF
Reverse Transfer Capacitance	C _{res}	f = 1MHz	-	79	-	
Total Gate Charge	Q_g	V _{CE} = 400V	-	171	-	
Gate - Emitter Charge	Q_{ge}	I _C = 80A	-	33	-	nC
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	59	-	
Turn - on Delay Time	t _{d(on)}	I _C = 80A, V _{CC} = 400V	-	45	-	
Rise Time	t _r	$V_{GE} = 15V, R_G = 10\Omega$	-	29	-	20
Turn - off Delay Time	$t_{d(off)}$	T _j = 25°C	-	201	-	ns
Fall Time	t _f	Inductive Load	-	34	-	
Turn - on Switching Loss	E _{on}	*E _{on} includes diode	-	2.65	-	
Turn - off Switching Loss	E_{off}	reverse recovery	-	1.80	-	mJ
Turn - on Delay Time	t _{d(on)}	I _C = 80A, V _{CC} = 400V	-	49	-	
Rise Time	t _r	$V_{GE} = 15V, R_G = 10\Omega$	-	34	-	20
Turn - off Delay Time	$t_{d(off)}$	T _j = 175°C	-	218	-	ns
Fall Time	t _f	Inductive Load	-	80	-	
Turn - on Switching Loss	E _{on}	*E _{on} includes diode	-	2.74	-	m l
Turn - off Switching Loss	E_{off}	reverse recovery	-	2.31	-	mJ
		I _C = 320A, V _{CC} = 520V				
Reverse Bias Safe Operating Area	RBSOA	$V_P = 650V, V_{GE} = 15V$	FULL SQUARE			-
		$R_G = 100\Omega, T_j = 175^{\circ}C$				
		$V_{CC} \le 360V$				
Short Circuit Withstand Time	t_{sc}	V _{GE} = 15V	2	-	-	μs
		T _j = 25°C				

•Electrical Characteristic Curves

Fig.1 Power Dissipation vs. Case Temperature

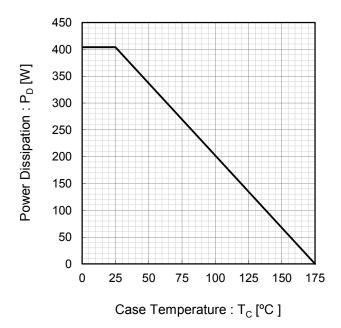


Fig.2 Collector Current vs. Case Temperature

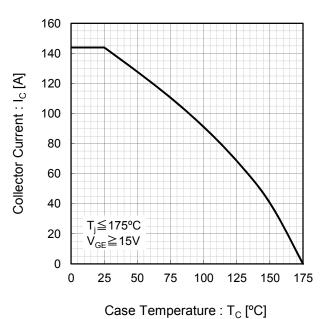


Fig.3 Forward Bias Safe Operating Area

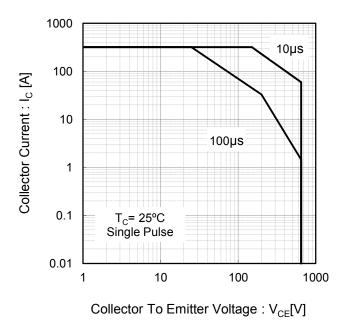
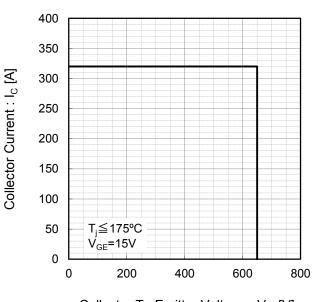


Fig.4 Reverse Bias Safe Operating Area



Electrical Characteristic Curves

Fig.5 Typical Output Characteristics

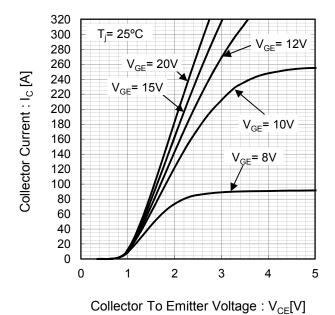
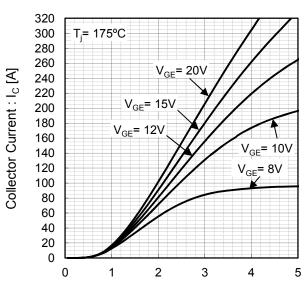


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage : V_{CE}[V]

Fig.7 Typical Transfer Characteristics

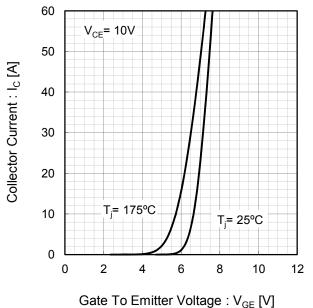
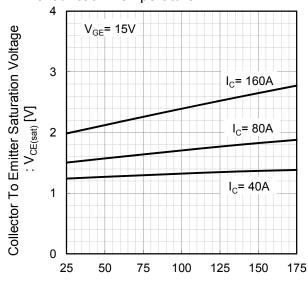


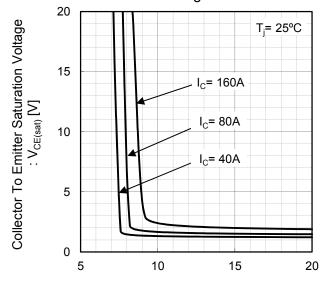
Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



Junction Temperature : T_i [°C]

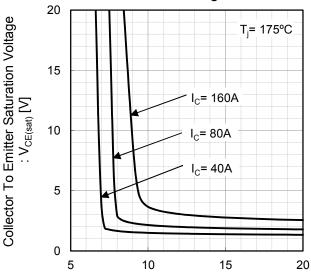
Electrical Characteristic Curves

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

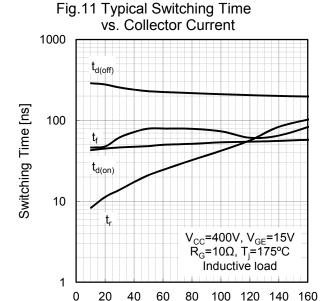


Gate To Emitter Voltage : V_{GE} [V]

Fig. 10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate To Emitter Voltage : V_{GE} [V]



Collector Current : I_C [A]

Fig.12 Typical Switching Time vs. Gate Resistance

1000 $t_{d(off)}$ 100 $t_{d(off)}$ $t_{d(on)}$ t_{d

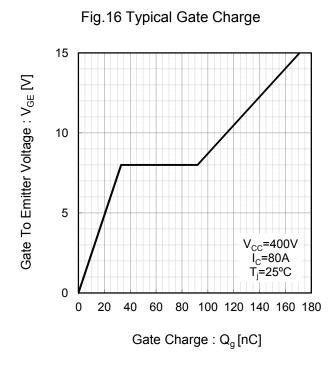
• Electrical Characteristic Curves

Fig.13 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ] E_{off} 1 0.1 V_{CC} =400V, V_{GE} =15V R_{G} =10 Ω , T_{j} =175°C Inductive load 0.01 0 20 100 120 140 160 40 60 Collector Current : I_C [A]

vs. Gate Resistance vs. Gate Resistance 10 E_{on} 1 E_{off} 0.1 $V_{cc}=400V, I_{c}=80A$ $V_{GE}=15V, T_{j}=175^{\circ}C$ Inductive load 0.01 0 10 20 30 40 50 Gate Resistance : $R_{G}[\Omega]$

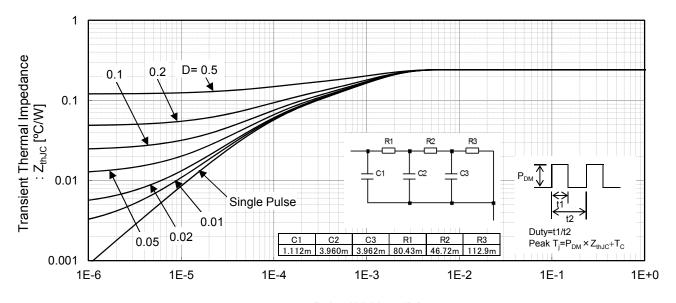
Fig.14 Typical Switching Energy Losses

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] Coes 100 Cres 10 f=1MHz V_{GE}=0V T,=25°C 0.01 0.1 1 10 100 Collector To Emitter Voltage : V_{CE}[V]



•Electrical Characteristic Curves

Fig.17 Typical IGBT Transient Thermal Impedance



Pulse Width: t1[s]

●Inductive Load Switching Circuit and Waveform

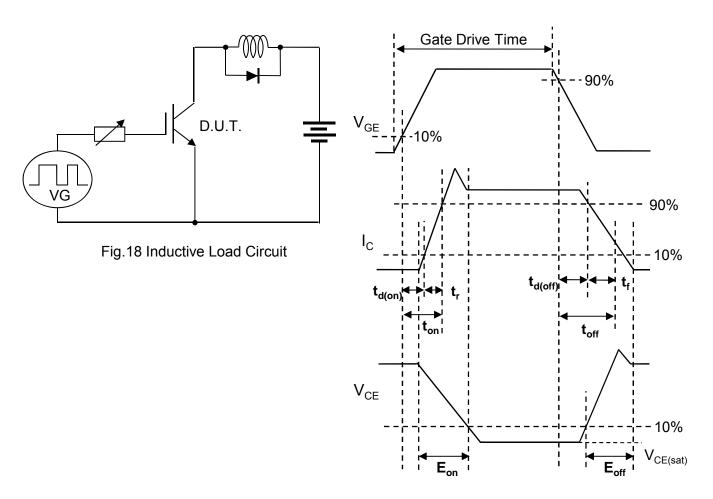


Fig.19 Inductive Load Waveform

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